MAIN MEMORY SYSTEM

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THE

OF UTAH

UNIVERSITY CS/ECE 6810: Computer Architecture



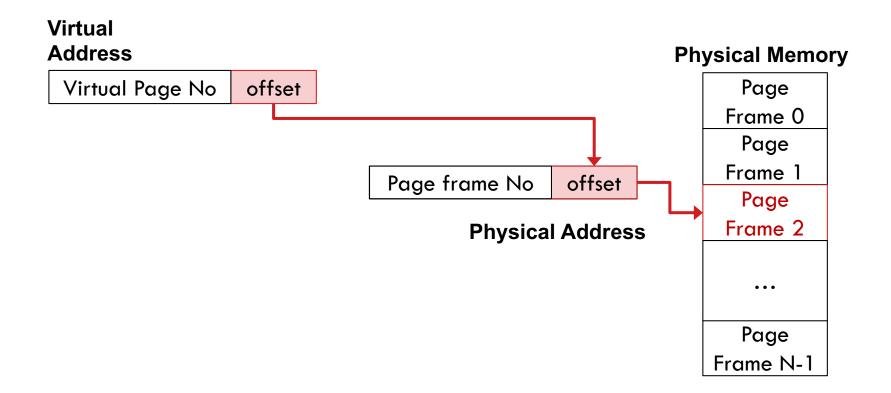
Announcement

Homework 4 submission deadline: Nov. 6th

- This and the following lectures
 - Dynamic random access memory (DRAM)
 - DRAM operations
 - Memory scheduling basics
 - Emerging memory technologies

Recall: Address Translation

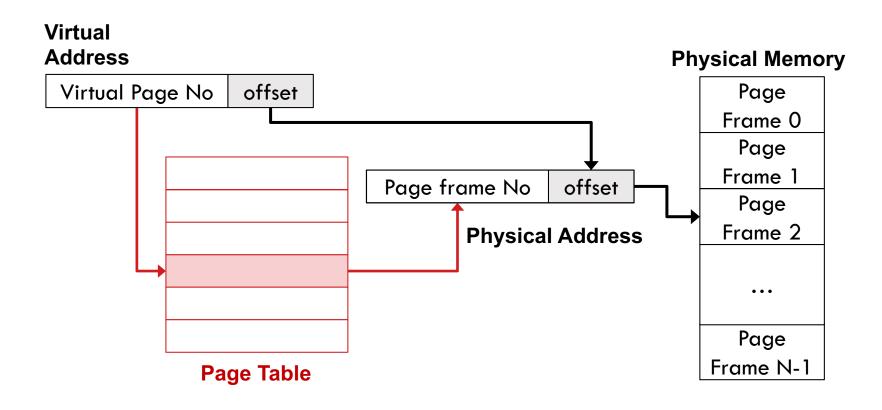
Exploit locality to reduce address translation time
Offset bits are copied from virtual address



Recall: Address Translation

Exploit locality to reduce address translation time

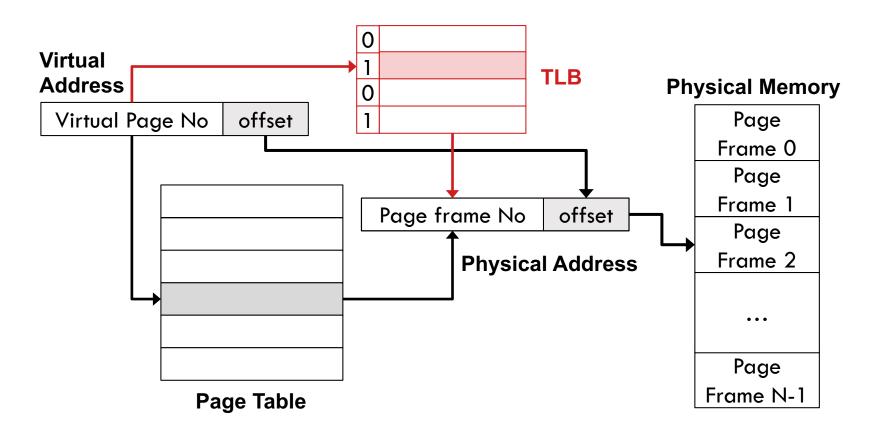
OS maintains the page table for address translation



Recall: Translation Lookaside Buffer

Exploit locality to reduce address translation time

Keep recent translation in a buffer for future references



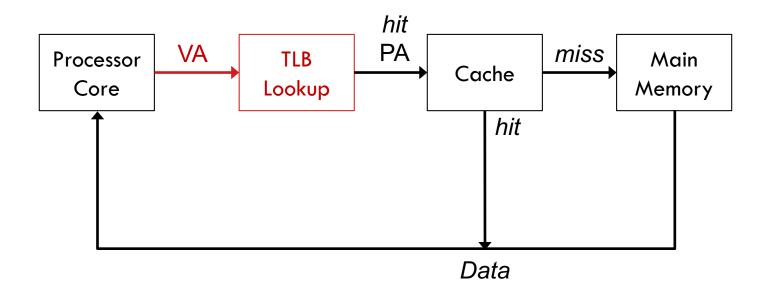
TLB in Memory Hierarchy

On a TLB miss, is the page loaded in memory?

Yes: takes 10's cycles to update the TLB

No: page fault

Takes 1,000,000's cycles to load the page and update TLB

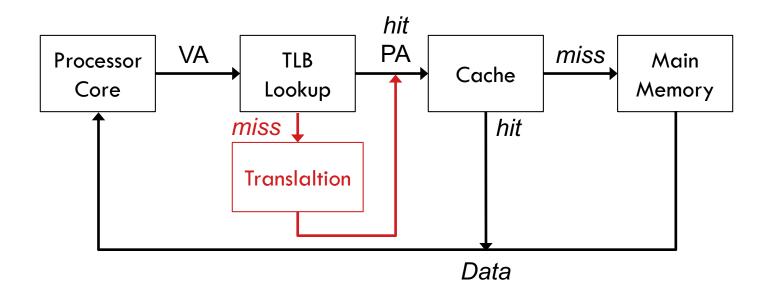


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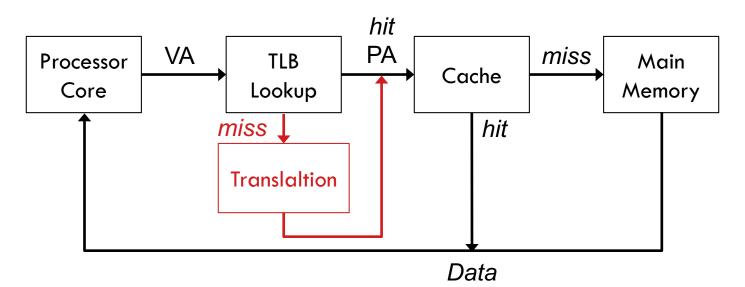
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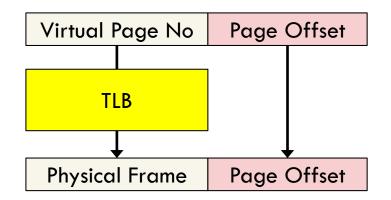
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Physically indexed, physically tagged: TLB on critical path!



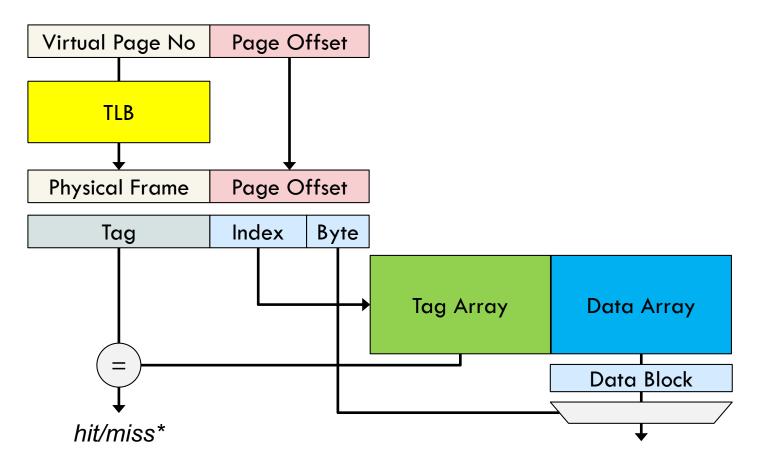
Physically Indexed Caches

Problem: increased critical path due to sequential access to TLB and cache



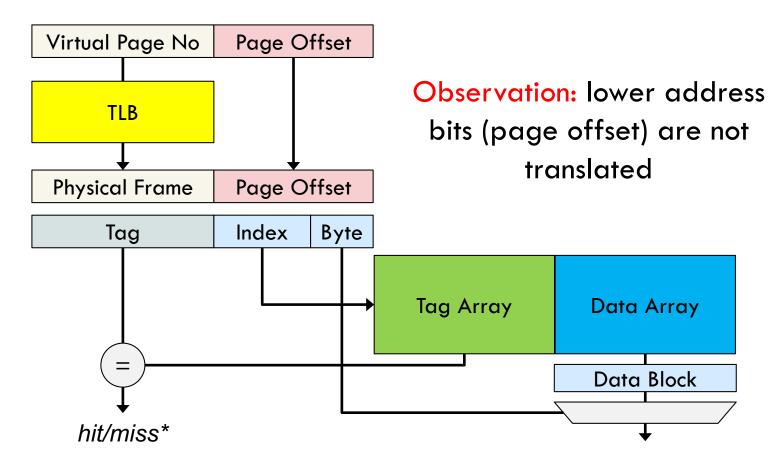
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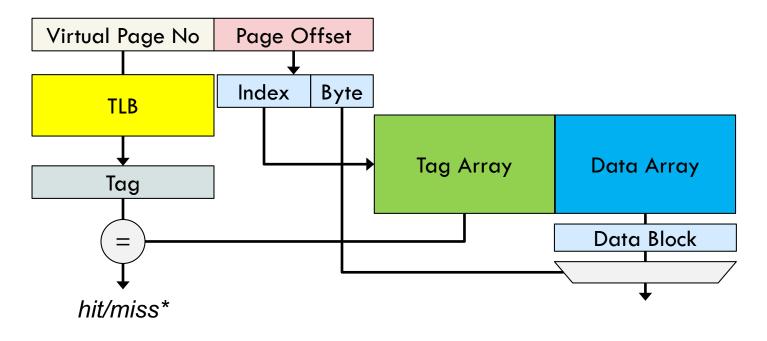
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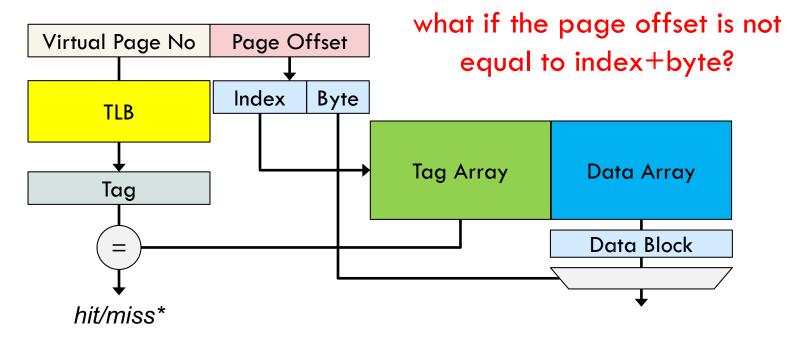
Virtually Indexed Caches

Idea: Index into cache in parallel with page number translation in TLB



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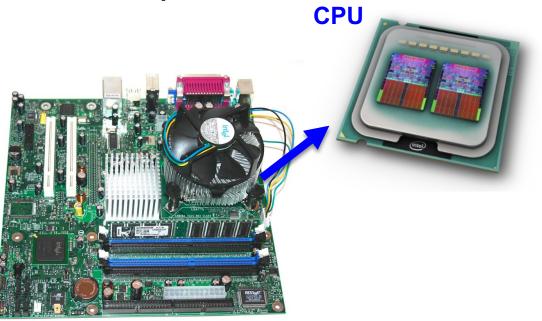




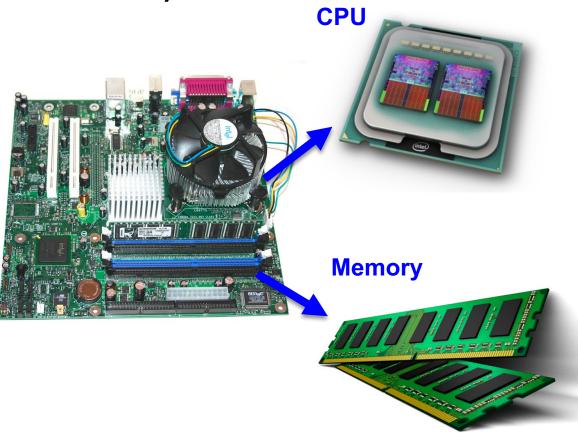
DRAM technology is commonly used for main memory



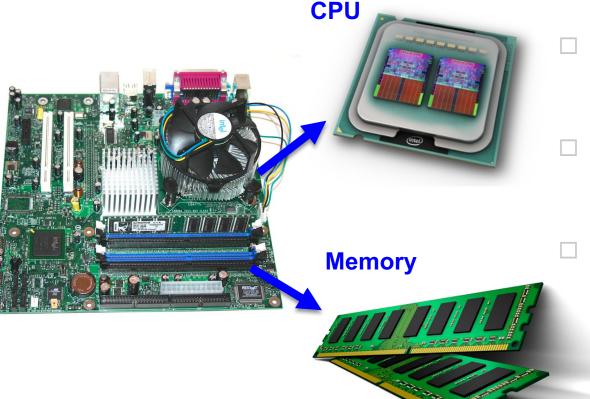
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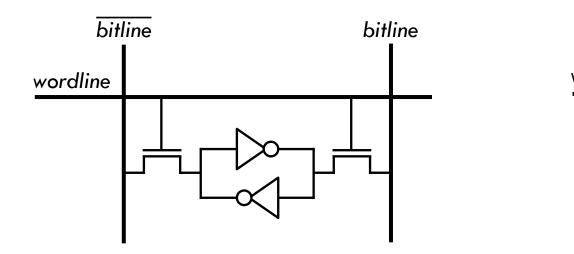


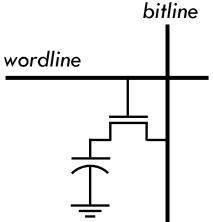
SRAM is used for caches
DRAM is used for main memory
DRAM is accessed on a TLB or last level cache miss

Static vs. Dynamic RAM

Static RAM (SRAM)

Dynamic RAM (DRAM)





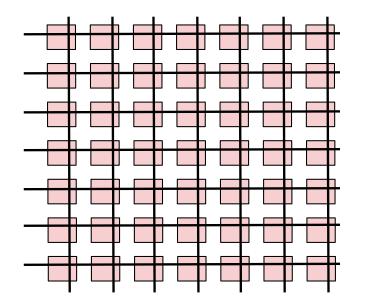
Static vs. Dynamic RAM

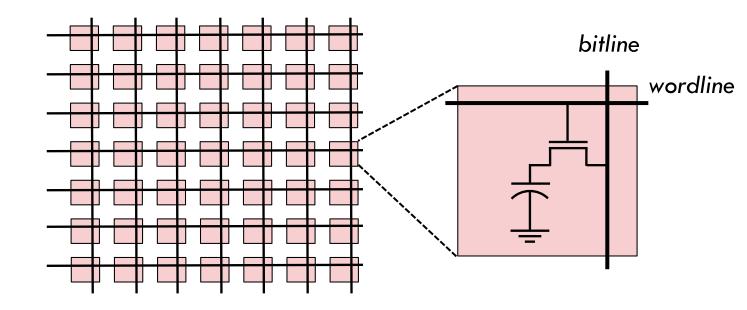
Static RAM (SRAM)

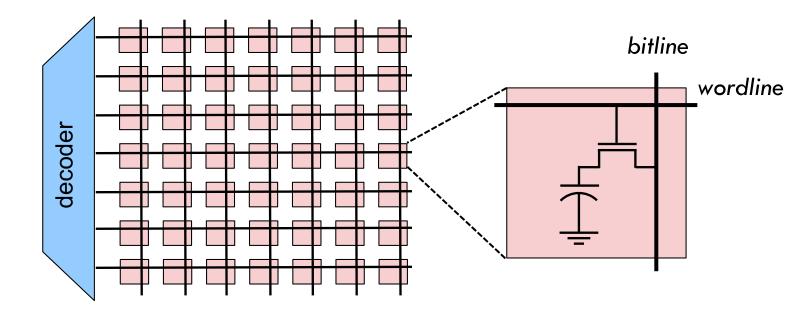
- Fast and leaky
 - 6 transistors per bit
 - Normal CMOS Tech.
- Static volatile
 - Retain data as long as powered on

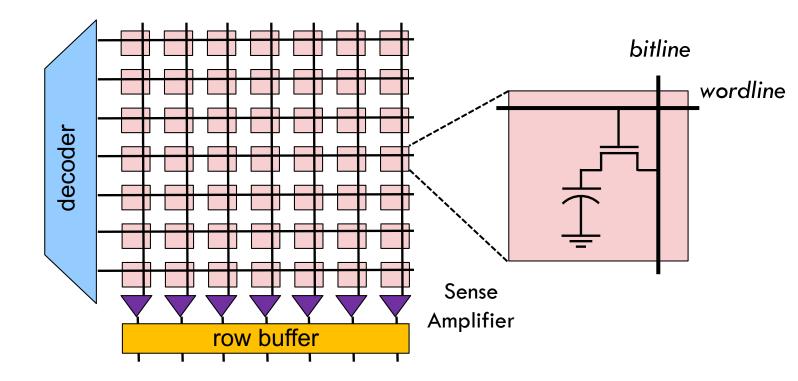
Dynamic RAM (DRAM)

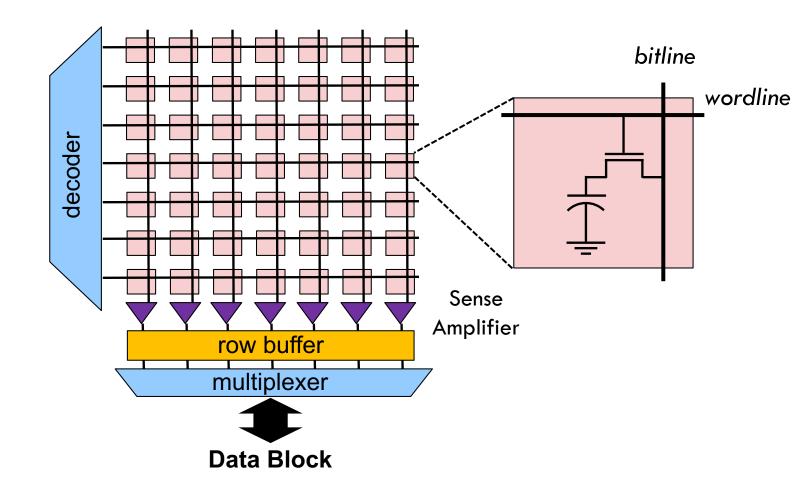
- Dense and slow
 - 1 transistor per bit
 - Special DRAM process
- Dynamic volatile
 - Periodic refreshing is required to retain data

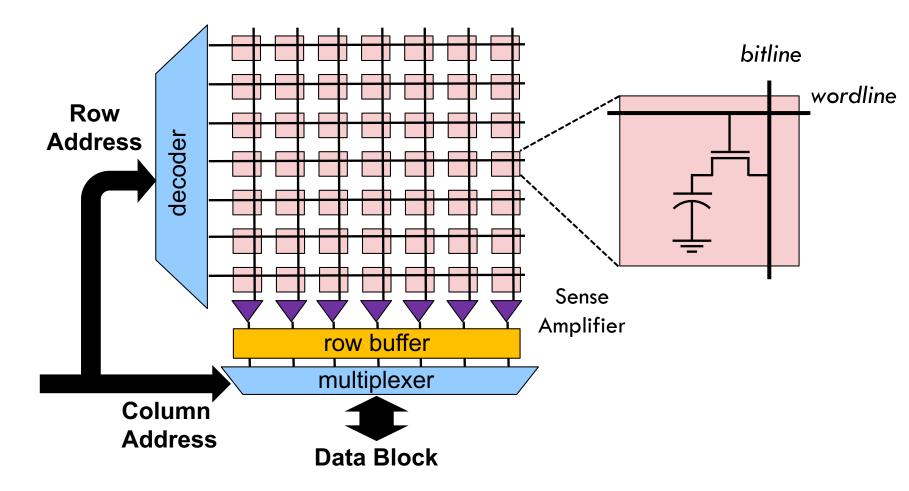


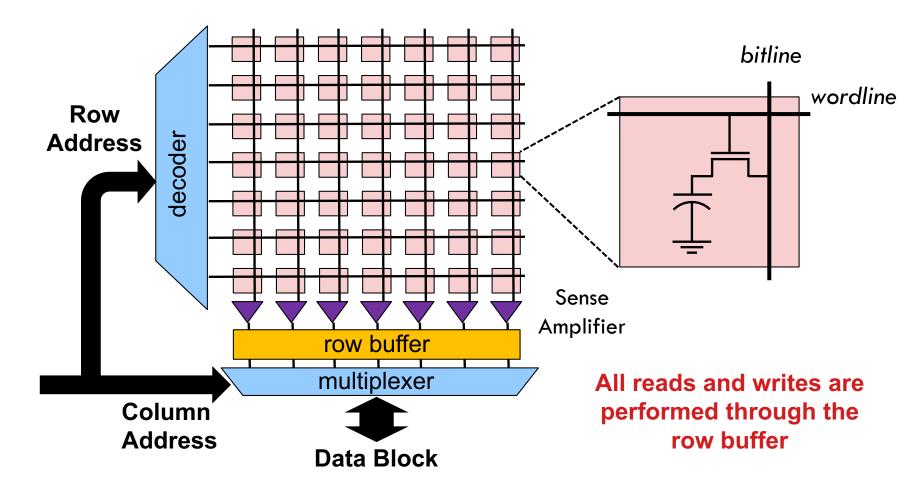






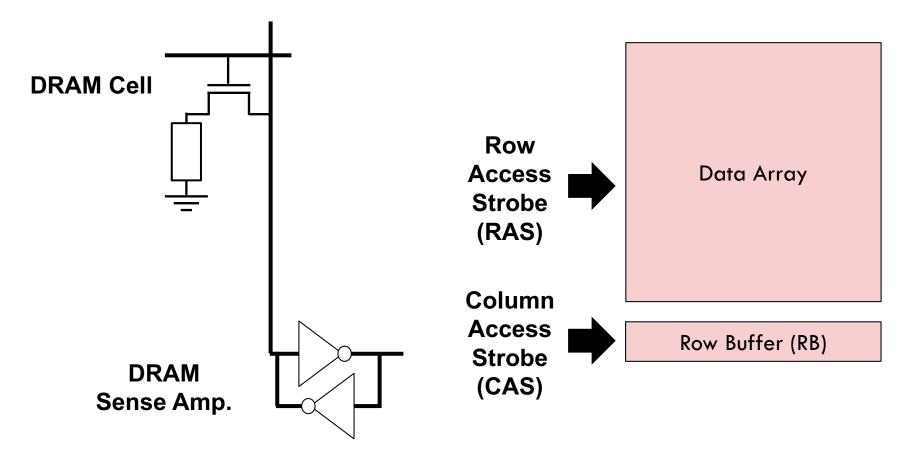


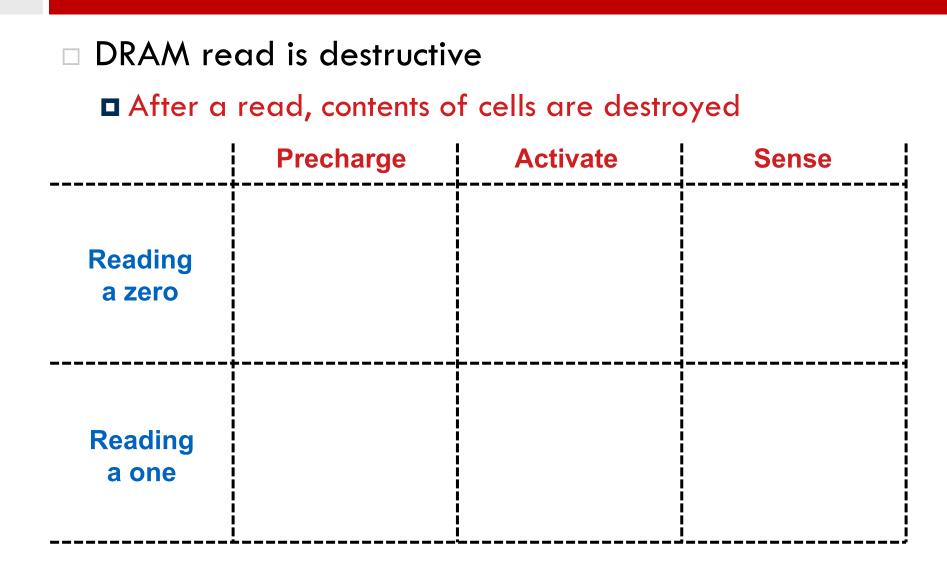




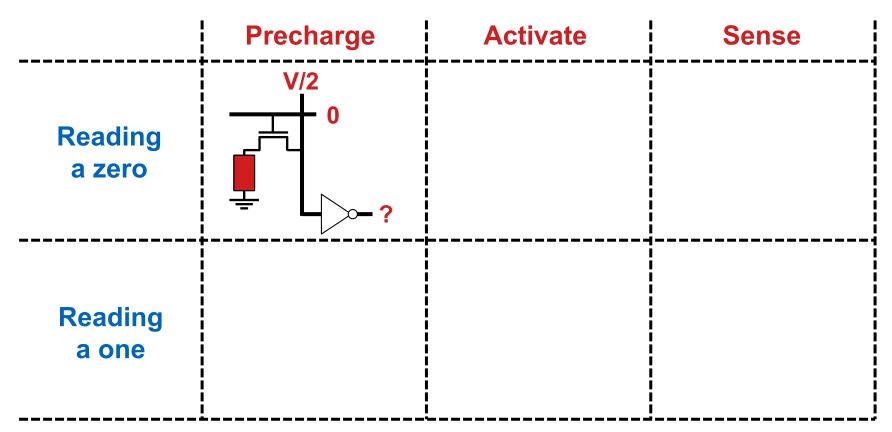
DRAM Row Buffer

All reads and writes are performed through RB

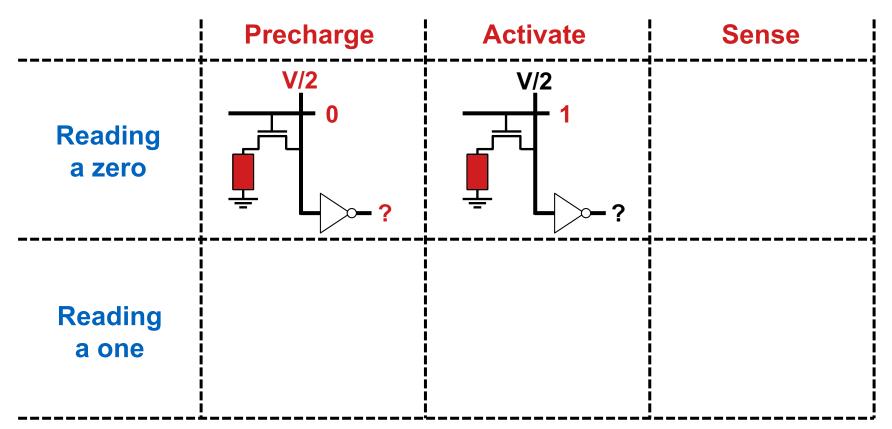




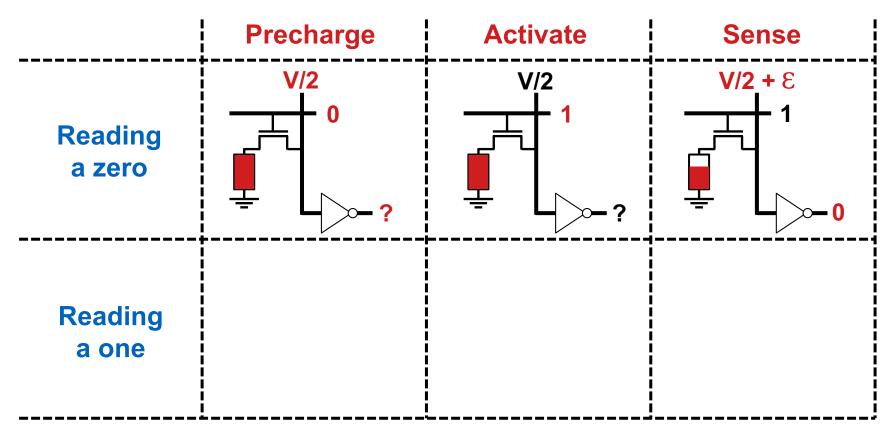




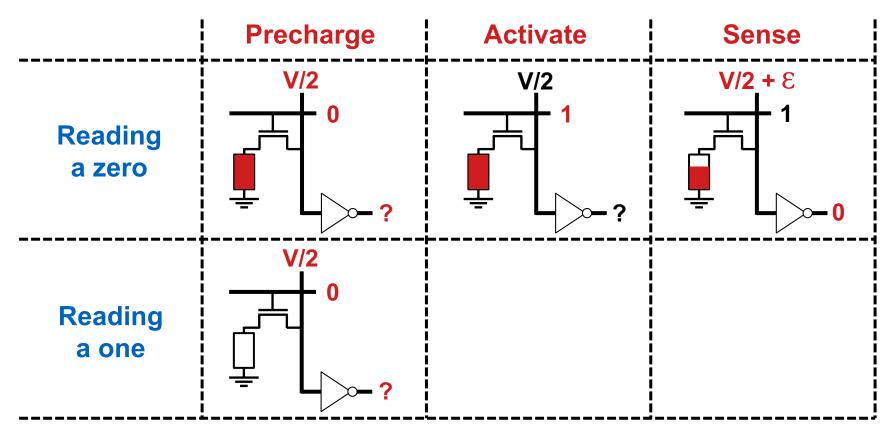
DRAM read is destructive



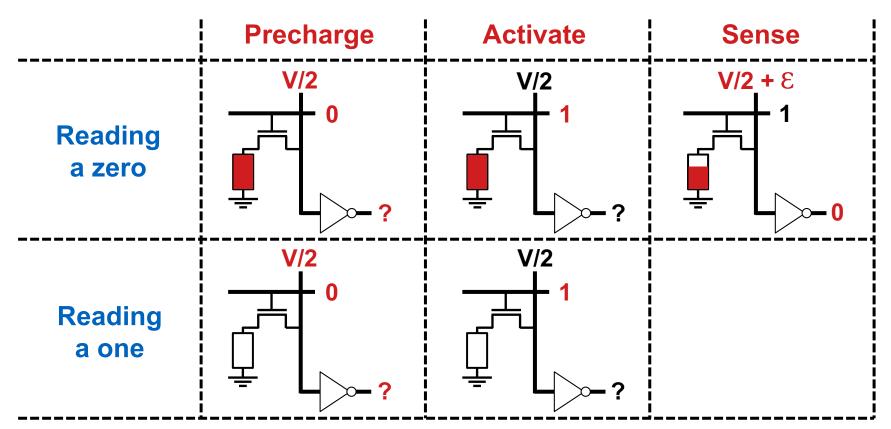
□ DRAM read is destructive



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